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FDA59N25 N-Channel UniFETTM MOSFET 250 V, 59 A, 49 mΩ

Features

- $R_{DS(on)}$ = 49 m Ω (Max.) @ V_{GS} = 10 V, I_D = 29.5 A
- Low Gate Charge (Typ. 63 nC)
- Low C_{rss} (Typ. 70 pF)
- 100% Avalanche Tested
- RoHS Compliant

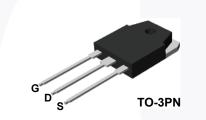
Applications

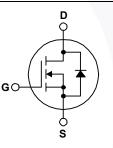
- PDP TV
- Uninterruptible Power Supply
- AC-DC Power Supply

April 2014

Description

UniFETTM MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FDA59N25	Unit	
V _{DSS}	Drain to Source Voltage			250	V
V _{DS(Avalanche)}	Repetitive Avalanche Volta	age	(Note 1,2)	300	V
V _{GSS}	Gate to Source Voltage			±30	V
	Drain Current	- Continuous (T _C = 25°C)		59	A
I _D		- Continuous (T _C = 100 ^o C)		35	
I _{DM}	Drain Current	- Pulsed	(Note 1)	236	А
E _{AS}	Single Pulsed Avalanche Energy		(Note 2)	1458	mJ
I _{AR}	Avalanche Current		(Note 1)	59	Α
E _{AR}	Repetitive Avalanche Energy		(Note 1)	39.2	mJ
dv/dt	Peak Diode Recovery dv/dt		(Note 3)	4.5	V/ns
P _D	Power Dissipation	(T _C = 25 ^o C)		392	W
		- Derate Above 25°C		3.2	W/ºC
T _J , T _{STG}	Operating and Storage Temperature Range			-55 to +150	°C
TL	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		Seconds	300	°C

Thermal Characteristics

Symbol	Parameter	FDA59N25	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.32	
$R_{\theta CS}$	Thermal Resistance, Case to Sink, Typ.	0.24	°C/W
$R_{ ext{ heta}JA}$	Thermal Resistance, Junction to Ambient, Max.	40	

•		Top Mark	Package	Packing Method	Reel Size	Та	pe Width	Qu	antity
		TO-3PN	<u> </u>		N/A		30	30 units	
Electric	al Chara	ICTERISTICS T _C = 25°C un	less otherwise n	oted					
Symbol		Parameter		Conditions		Min.	Тур.	Max	Unit
Off Charac	cteristics				ľ		•		
BV _{DSS}	Drain-Source Breakdown Voltage		V _{GS} = 0	V _{GS} = 0 V, I _D = 250 μA		250			V
ΔΒV _{DSS} / ΔT _J			I _D = 250	$I_D = 250 \ \mu$ A, Referenced to 25°C			0.25		V/°C
I _{DSS}	Zero Gate Voltage Drain Current			$V_{DS} = 250 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = 200 \text{ V}, T_{C} = 125^{\circ}\text{C}$				1 10	μΑ μΑ
I _{GSSF}	Gate-Body	Leakage Current, Forward	V _{GS} = 3	0 V, V _{DS} = 0 V		-		100	nA
I _{GSSR}	Gate-Body	Leakage Current, Reverse	V _{GS} = -3	$V_{GS} = -30 \text{ V}, V_{DS} = 0 \text{ V}$				-100	nA
On Charac	cteristics								
V _{GS(th)}	Gate Threshold Voltage		V _{DS} = V	V _{DS} = V _{GS} , I _D = 250 μA		3.0		5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance		V _{GS} = 1	V _{GS} = 10 V, I _D = 29.5 A			0.041	0.049	Ω
9 _{FS}	Forward Transconductance V _{DS}		V _{DS} = 4	0 V, I _D = 29.5 A			45		S
Dynamic C	Characteristi	cs			ľ		•		
C _{iss}	Input Capa	Input Capacitance Output Capacitance		V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz			3090	4020	pF
C _{oss}	Output Cap						630	820	pF
C _{rss}	Reverse Transfer Capacitance						70	110	pF
Switching	Characterist	tics			ľ		•		
t _{d(on)}	Turn-On Delay Time		V _{DD} = 1	V _{DD} = 125 V, I _D = 59 A			70	150	ns
t _r	Turn-On Ri	se Time	V _{GS} = 1	V _{GS} = 10 V, R _G = 25 Ω (Note 4)			480	970	ns
t _{d(off)}	Turn-Off De	elay Time					90	190	ns
t _f	Turn-Off Fa	all Time					170	350	ns
Qg	Total Gate	Charge	V _{DS} = 2	$V_{DS} = 200 \text{ V}, I_D = 59 \text{ A}$ $V_{GS} = 10 \text{ V}$ (Note 4)			63	82	nC
Q _{gs}	Gate-Sourc	ce Charge	V _{GS} = 1				18.5		nC
Q _{gd}	Gate-Drain	Charge					30		nC
	rce Diode Ch	naracteristics and Maximu	m Ratings						•
I _S Maximum Continuous Drain-Source Diod		ode Forward	I Current				59	Α	
I _{SM}	Maximum F	Pulsed Drain-Source Diode	Forward Cur	prward Current				236	Α
V _{SD}	Drain-Sour	ce Diode Forward Voltage	V _{GS} = 0	V, I _S = 59 A				1.4	V
t _{rr}	Reverse Re	ecovery Time	$V_{GS} = 0$	$V_{GS} = 0 V, I_S = 59 A$ $V_{GS} = 0V, I_S = 59 A,$			190		ns
Q _{rr}	Reverse Re	ecovery Charge	dl _F /dt =1	100 A/μs	-		4.4		μC

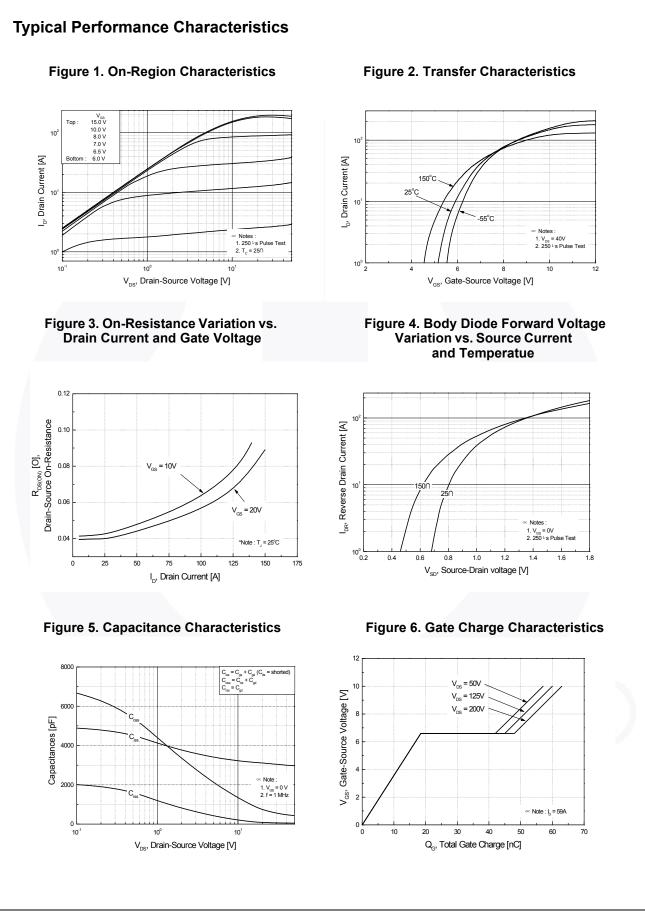
1. Repetitive rating: pulse-width limited by maximum junction temperature.

2. L = 0.67 mH, I_{AS} = 59 A, V_{DD} = 50 V, R_G = 25 Ω , starting T_J = 25°C.

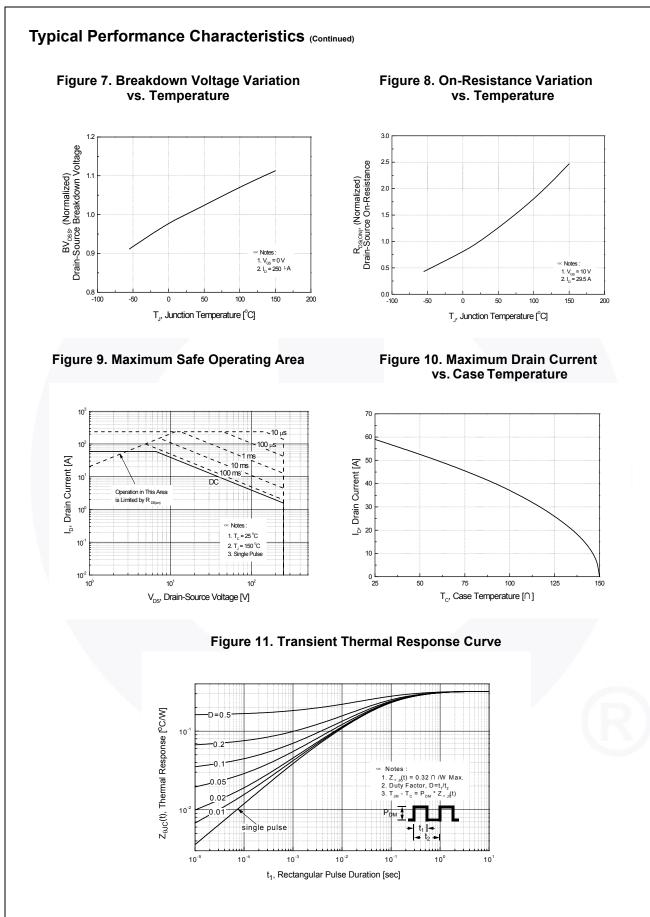
3. I_{SD} \leq 59 A, di/dt \leq 200 A/µs, V_{DD} \leq BV_{DSS}, starting T_J = 25°C.

4. Essentially independent of operating temperature typical characteristics.

2



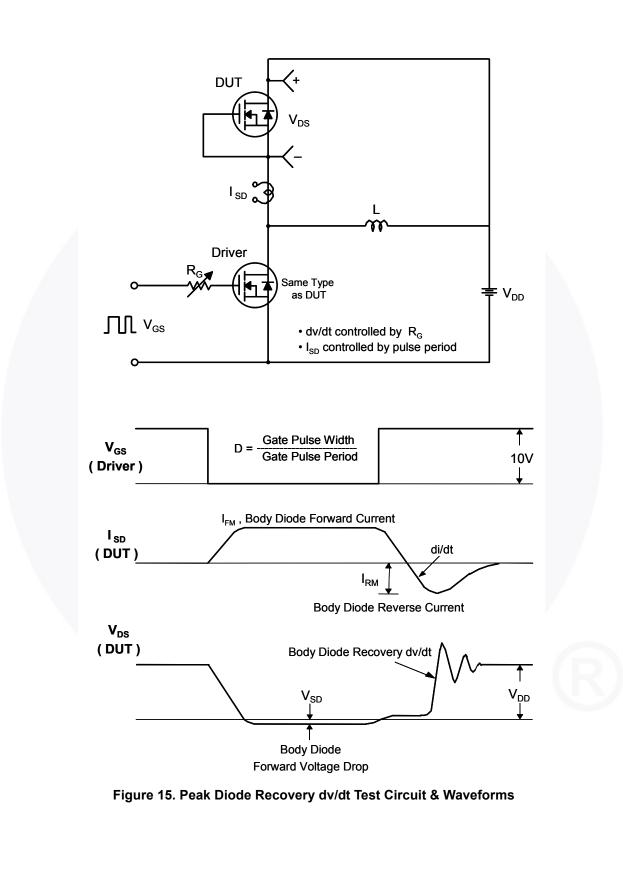
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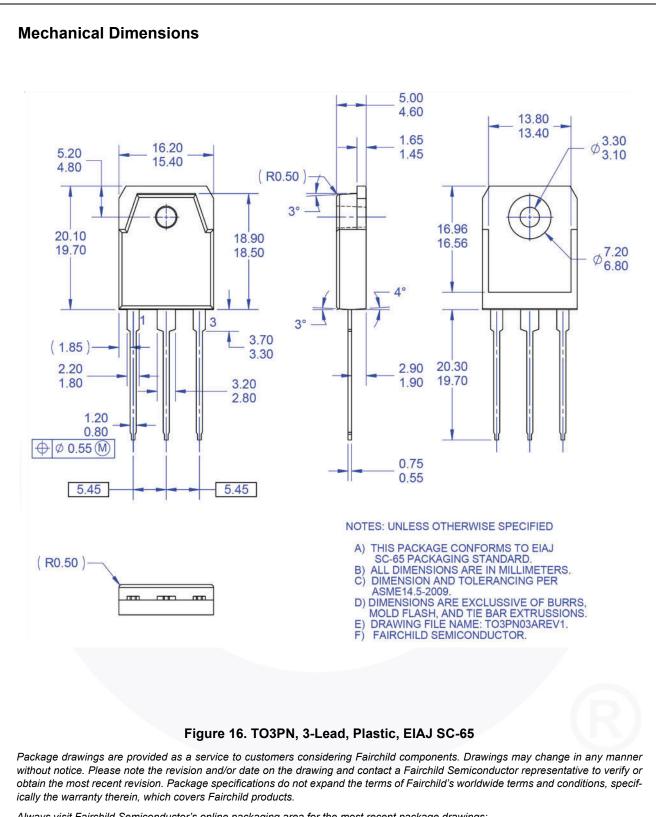


4

V_{GS} Ş R Qg F V_{DS} Qgs Q_{gd} DUT I_G = const. Charge Figure 12. Gate Charge Test Circuit & Waveform R VDS VDS 90% О V_{DD} R_{G} 10% V_{GS} DUT V_{GS} ∏ 0 Figure 13. Resistive Switching Test Circuit & Waveforms BV_{DSS} BV_{DSS} - V_{DD} L $E_{AS} = \frac{1}{2} L I_{AS}^2$ VDS $\mathsf{BV}_{\mathsf{DSS}}$ D I_{AS} R_G = V_{DD} $I_{D}(t)$ DUT V_{DD} V_{DS}(t) 10V Time t_p Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

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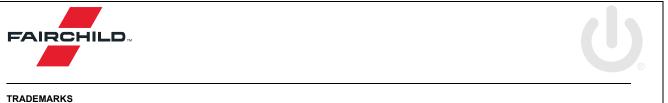




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